

REMARKS/ARGUMENTS

Claim 1 has been amended with the limitations of claim 3 as requested by the examiner; claim 3 has been canceled. Claims 2 and 4 -35 are now dependent upon an acceptable base claim. Claims 36 - 73 are previously allowed.

Claims Rejections-35 USC 103(a)

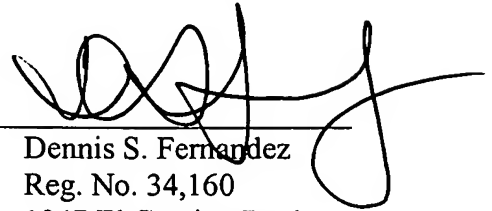
Applicants respectfully disagree with the use of Ramdani, 2003/0027409, as a meaningful reference. Please note that Ramdani teaches the growth of single crystal germanium over a single crystal metal oxide layer. Ramdani also teaches a discrete germanium transistor device being connected to a discrete silicon device. Ramdani neither teaches nor suggests the growth of a germanium layer in contact with a silicon layer, thereby forming a heterojunction; neither does he teach nor suggest the operating of a heterojunction through a plurality of contacts to a germanium layer and a silicon layer in contact with each other. Also please note that element 124 in Figure 30 is "... buffer layer 124 typically is a monocrystalline metal oxide or nitride layer..." ¶[0102], 4th sentence.

Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Respectfully submitted,

Fernandez & Associates

By

A handwritten signature in black ink, appearing to read 'Dennis S. Fernandez', written over a horizontal line.

Dennis S. Fernandez

Reg. No. 34,160

1047 El Camino Real

Menlo Park, CA 94025

Customer No: **22877**

Phone: (650) 325-4999

Fax: (650) 325-1203

Email: iploft@iploft.com